

34. (New) The method, as recited in claim 19, wherein the active etchant is nitrogen and hydrogen.

35. (New) The method, as recited in claim 19, further comprising depositing polymer from the fluorocarbon on the hardmask to reduce hardmask sputtering.

36. (New) The method, as recited in claim 19, further comprising depositing polymer from the fluorocarbon on sidewalls of the feature to reduce profile bowing.

37. (New) The method, as recited in claim 19, further comprising etching an opening in the hardmask with the active etchant, wherein sputtering some of the hardmask occurs during the etching an opening in the hardmask, and wherein the forming a volatile compound occurs during the etching an opening in the hardmask, wherein the active etchant etches the hardmask opening and wherein the active etchant is selected from the group consisting of hydrogen and ammonia.

REMARKS

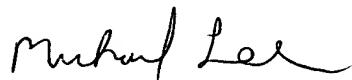
Claims 1-4, 6, and 8-18 have been cancelled. Claims 19-37 have been added.

The Examiner rejected claims 2-4, 6, and 12-14 under 35 U.S.C. § 112, first paragraph, as containing subject matter which is not described in the specification. The Examiner stated that regarding claim 2, line 2, “silicon-free benzocyclobutene” is new matter. These claims have been cancelled, however new claim 24 recites “silicon-free benzocyclobutene”. Page 2, lines 20-21, of the application states that SiLK is a silicon-free BCB (benzocyclobutene).

Applicants believe that all pending claims, as amended, are allowable and respectfully request a Notice of Allowance for this application from the Examiner. Should the Examiner

believe that a telephone conference would expedite the prosecution of this application, the undersigned can be reached at telephone number (831) 655-2300.

Respectfully submitted,
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